

A<sup>1</sup>  
This application is related to Japanese application No. 2000-371625 filed on  
December 6, 2000, whose priority is claimed under 35 USC §119.

IN THE CLAIMS

Please cancel <sup>✓</sup> non-elected claims 6-9, without prejudice in view of the Restriction Requirement.

Please substitute the following amended claim(s) for corresponding claim(s) previously presented. A copy of the amended claim(s) showing current revisions is attached.

A<sup>2</sup>  
1. (Amended) A semiconductor device comprising:  
regions for forming a plurality of functional blocks;  
a region for forming wiring layers for connecting the functional blocks,  
wherein each of the regions for forming the functional blocks includes a multilayer wiring, and  
wherein the region for forming the wiring layers for connecting adjacent functional blocks includes a coaxial line comprising an inner signal line and an outer ground line surrounding the signal line via an insulating film as viewed cross sectionally, so that the inner signal line and outer ground line have a common axis along at least a portion of a length of the coaxial line.

2. (Amended) A semiconductor device according to claim 1, wherein a bottom surface of a wiring in the multilayer wiring provided in the region for forming the functional block is on the same plane as a bottom surface of the coaxial line provided in the region for forming the wiring layers for connecting the functional blocks.

3. (Amended) A semiconductor device comprising:

regions for forming a plurality of functional blocks; and

a region for forming wiring layers for connecting the functional blocks,

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cont.  
wherein each of the regions for forming the functional blocks includes a multilayer wiring, and the region for forming the wiring layers for connecting the functional blocks includes a transmission line comprising a signal line and ground lines and/or power source lines formed above and below the signal line, respectively, as viewed cross sectionally, to sandwich the signal line via an insulating film.

4. (Amended) A semiconductor device according to claim 3, wherein a bottom surface of a wiring layer in the multilayer wiring provided in the region for forming the functional block is on the same plane as a bottom surface of the ground line or power source line located below the transmission line provided in the region for forming the wiring layers for connecting the functional blocks.

5. (Amended) A semiconductor device comprising: